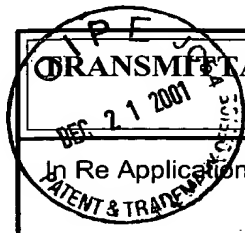


1762

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))		Docket No. 11471-US	
In Re Application Of: Luc Ouellet et al.			
Serial No. 09/867,662	Filing Date 05/31/01	Examiner	Group Art Unit 1762
Title: METHOD OF DEPOSITING OPTICAL FILMS			
<p style="text-align: center;">Address to: Assistant Commissioner for Patents Washington, D.C. 20231</p> <p style="text-align: center;">37 CFR 1.97(b)</p> <p>1. <input checked="" type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application; within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or, before the mailing date of a first Office Action on the merits, whichever event occurs last.</p> <p style="text-align: center;">37 CFR 1.97(c)</p> <p>2. <input type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed after three months of the filing of a national application, or the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or after the mailing date of a first Office Action on the merits, whichever occurred last but before the mailing date of either:</p> <p style="margin-left: 40px;">1. a Final Action under 37 CFR 1.113, or</p> <p style="margin-left: 40px;">2. a Notice of Allowance under 37 CFR 1.311,</p> <p style="margin-left: 40px;">whichever occurs first.</p> <p>Also submitted herewith is:</p> <p><input type="checkbox"/> a certification as specified in 37 CFR 1.97(e);</p> <p style="text-align: center;">OR</p> <p><input type="checkbox"/> the fee set forth in 37 CFR 1.17(p) for submission of an Information Disclosure Statement under 37 CFR 1.97(c).</p>			



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Docket No.
11471-US

In Re Application Of: Luc Ouellet et al.

Serial No.
09/867,662

Filing Date
05/31/01

Examiner

Group Art Unit
1762

Title:

METHOD OF DEPOSITING OPTICAL FILMS

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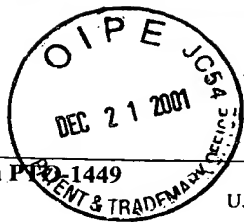
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APPLICANT

Luc OUELLET et al.

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U.S. PATENT DOCUMENTS

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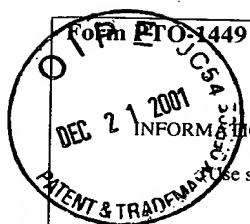
OTHER DOCUMENTS (Including Author, title, Date, Pertinent Pages, Etc.)

	D.K.W. Lam, "Low temperature plasma chemical vapor deposition of silicon oxynitride thin-film waveguides", Applied Optics, Vol. 23, No. 16, August 15, 1984, pp. 2744-2746.
	Franco Bruno et al., "Plasma-enhanced chemical vapor deposition of low-loss SiON optical waveguides at 1.5- μ m wavelength", Applied Optics, Vol. 30, No. 31, November 1, 1991, pp.4560-4564.
	K. Imoto, et al., "High refractive index difference and low loss optical waveguide fabricated by low temperature processes", Electronics Letters, Vol. 29, No. 12, June 10, 1993, pp. 1123-1124.
	Q. Lai et al., "Simple technologies for fabrication of low-loss silica waveguides", Electronics Letter, March 31, 1992.
	Yuan-Kuang Tu, et al., "Single-mode SiON/SiON ₂ /Si Optical Waveguides Prepared by Plasma-Enhanced Chemical Vapor Deposition", Fiber and Integrated Optics, Vol. 14, pp.133-139.
	S. Yokoyama et al., "Optical waveguides on silicon chips", J.Vac. Sci. Technol. A13(3), May/Jun1995, pp.629-635.
	O.P. Agnihotri et al., "Silicon Oxynitride Waveguides for Optoelectronic Integrated Circuits", Jpn. Appl., vol 36, Part 1, No. 11, November 1997, pp. 6711-6713.
	Daniel P. Poenar et al., "Optical properties of thin-film silicon-compatible materials", Applied Optics, Vol36, No. 21, July 20, 1997, pp.5122-5128.
	I. Pereyra et al., "High quality low temperature DPECVD silicon dioxide", Journal of Non-Crystalline Solids, 212, 1997, pp. 225-231.
	M.I. Alayo, et al., "Thick SiO _x N _y and SiO ₂ films obtained by PECVD techniques at low temperature", Thin Film Solids, 332, 1998, pp. 40-45.
	R.German et al., "Silicon-Oxynitride Layer for Optical Waveguide Applications", The Electronic Society Inc., Vol. 99-1, May 199, Abstract No. 137.
	K. Worhoff et al., "Plasma enhanced chemical vapor deposition silicon oxynitride optimized for application in integrated optics", Sensor and Actuators, 74, 1999, pp. 9-12.

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DATE CONSIDERED

* Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Drawn line through citation, not in conformance and not considered. Include copy of this form with next communication to applicant.



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APPLICANT

Luc OUELLET et al.

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U.S. PATENT DOCUMENTS

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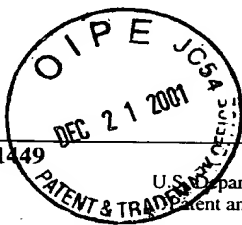
OTHER DOCUMENTS (Including Author, title, Date, Pertinent Pages, Etc.)

	A.J. Kenyon et al., "A luminescence study of silicon-rich silica and rare-earth doped silicon-rich silica", Electrochemical Society Proceedings Vol. 91-11, pp. 304-318.
	M. Hoffmann et al., "Low temprature, nitrogen doped waveguides on silicon with small core dimensions fabriacated by PECVD/RIE", Waveguide Technology, WeC2, pp.299-301.
	M. Hoffmann et al., "Low-Loss Fiber-Matched Low-Temperature PECVD Waveguides with Small-Core Dimensions for Optical Communications Systems, IEEE Photonics Technology Letters, Vol. 9, No. 9, September 1997, pp. 1238-1240.
	K. Kapser et al., "Rapid Deposition of High-Quality Silicon-Oxynitride Waveguides, IEEE Transactions Photonics Technology Letters, Vol. 3, No. 12, December 1991, pp. 1096-1098.
	D.A.P. Bulla et al., "Deposition of thick TEOS PECVD silicon oxide layers for integrated optical waveguide applications", Thin Solid Films, 334, 1998, pp. 60-64.
	E.S. Bulat et al., "Fabrication of waveguides using low-temperature plasma processing techniques", J. Vac. Sci. Techol. A 11(4) Jul/Aug 1993, pp.1268-1274.
	M.V> Bazylenko et al. "Fabrication of Low-Temperature PECVD Channel Waveguides with Significantly Improved Loss in the 1.50-1.55- μ m Wavelength Range, IEE Photonics Technology Letters, Vol. 7, No. 7, July 1995, pp. 774-776.
	M.V. Bazylenko et al., "Pure and fluorine-doped silica films deposited in a hollow cathode reactor for integrated optic applications", J. Vac. Sci. Technol. A 14(2), Mar/Apr 1996, pp. 336-345
	A. Durandet et al., "Silica buried channel waveguides fabricated at low temperature using PECVD", Electronics Letters, Vol. 32, No. 4, February 15, 1996, pp.326-327.
	R.W. Boswell et al., "Deposition of silicon dioxide films using the helicon diffusion reactor for integrated optics applications", Plasma Processing of Semiconductors, 1997, pp.433-475.
	S. Valette et al., "New Integrated Optical Multiplexer-Demultiplexer Realized on Silicon Substrate, ECIO87, May 1987, pp.145-147.
	S. Valette, "State of the art of integrated optics technology at LETI for achieving passive optical components", Journal of Modern Optics, Vol. 35, No. 6, 1998, pp. 993-1005.

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DATE CONSIDERED

* Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609. Drawn line through citation, not in conformance and not considered. Include copy of this form with next communication to applicant.



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				FILING DATE May 31, 2001		GROUP	
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FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub Class	Translation Yes No
OTHER DOCUMENTS (Including Author, title, Date, Pertinent Pages, Etc.)							
		G. Grand et al., "Low-Loss PECVD Silica Channel Waveguides for Optical Communications", Electronic Letters, Vol. 26, No. 25, December 6 1990, pp. 2135-21-37.					
		S.M. Ojha et al., "Simple method of fabricating polarisation-insensitive and very low crosstalk AWG grating devices", Electronic Letters, Vol. 34, No. 1, January 8, 1998, pp. 78-79.					
		C.M. Johnson et al., "Thermal annealing of waveguides formed by ion implantation of silica-on-Si", Nuclear Instruments and Methods in Physics Research B 141, 1998, pp. 670-674.					
		Karen Liu et al., "Hybrid optoelectronic digitally tunable receiver", SPIE, Vol. 2402, pp. 104-114.					
		Rene M. de Ridder et al., "Silicon Oxynitride Planar Waveguiding Structure for Application in Optical Communication", IEEE Journal of Selected Topics in Quantum Electronics, Vol. 4, No. 6, Nov/Dec 1998, pp. 930-936.					
		B. J. Offrein, "Wavelength Tunable Optical Add-After-Drop Filter with Flat Passband for WDM Networks", IEEE Photonics Technology Letters, Vol. 11, No. 2, February 1999, pp. 239-241.					
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